CNB1001

Reflective photosensor

For contactless SW and object detection

Overview

CNB1001 is a small, thin SMD-compatible reflective photosensor consisting of a high efficiency GaAs infrared light emitting diode which is integrated with a high sensitivity Si phototransistor in a single resin package.

■ Features

- Reflow-compatible reflective photosensor
- Ultraminiature, thin type: 2.7 mm × 3.4 mm (height: 1.5 mm)
- Visible light cutoff resin is used

■ Absolute Maximum Ratings $T_a = 25$ °C

F	Symbol	Rating	Unit	
Input (Light emitting diode)	Power dissipation *1	P_{D}	75	mW
	Forward current	I _F 50		mA
	Reverse voltage	V _R	6	V
Output (Photo transistor)	Collector-emitter voltage (Base open)	V _{CEO}	35	V
	Emitter-collector voltage (Base open)	V _{ECO}	6	V
	Collector current	I_{C}	20	mA
	Collector power dissipation *2	$P_{\rm C}$	75	mW
Operating ambient temperature		T _{opr}	-25 to +85	°C
Storage temperature	T _{stg}	-40 to +100	°C	

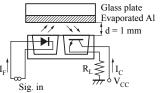
Note) *1: Input power derating ratio is 1.0 mW/°C at $T_a \ge 25$ °C.

■ Electrical-Optical Characteristics $T_a = 25$ °C±3°C

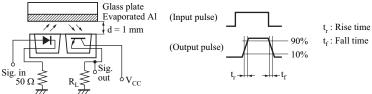
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Input characteristics	Reverse current	I_R	$V_R = 3 V$			10	μА
	Forward voltage	V _F	$I_F = 20 \text{ mA}$		1.2	1.4	V
Output characteristics	Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 20 \text{ V}$			100	nA
Transfer characteristics	Collector current *1	I_{C}	$V_{CC} = 2 \text{ V}, I_F = 4 \text{ mA},$ $R_L = 100 \Omega, d = 1 \text{ mm}$	23		160	μА
	Drain current	I_D	$V_{CC} = 2 \text{ V}, I_F = 4 \text{ mA}, R_L = 100 \Omega$			100	nA
	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 20 \text{ mA}, I_C = 0.1 \text{ mA}$			0.4	V
	Rise time *2	t _r	$V_{CC} = 5 \text{ V}, I_{C} = 0.1 \text{ mA},$		30		μs
	Fall time *2	t_{f}	$R_{\rm L} = 1000\Omega$		40		μs

Note) 1. Input and output are handled electrically.

- 2. This device is designed by disregarding radiation.
- 3. *1: Output current measurement circuit

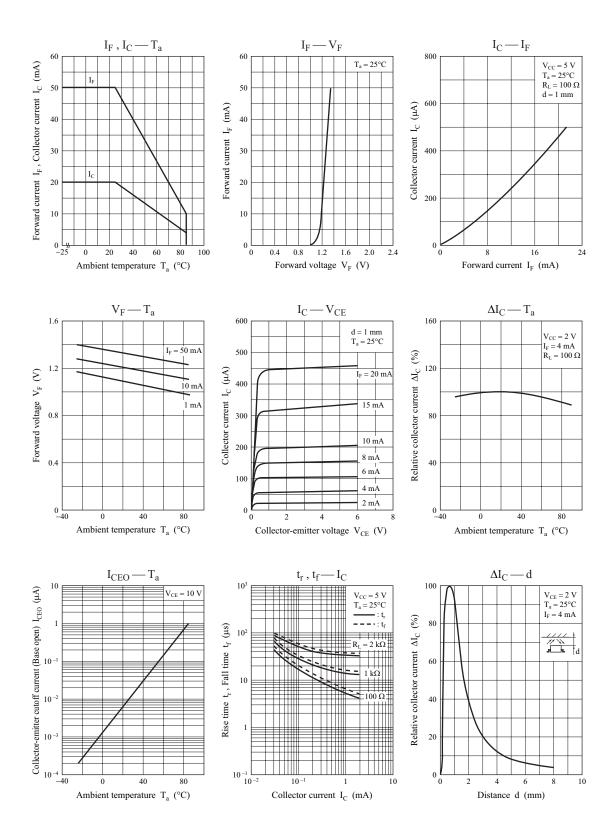


*2: Switching time measurement circuit



^{*2:} Output power derating ratio is 1.0 mW/°C at $T_a \ge 25$ °C.

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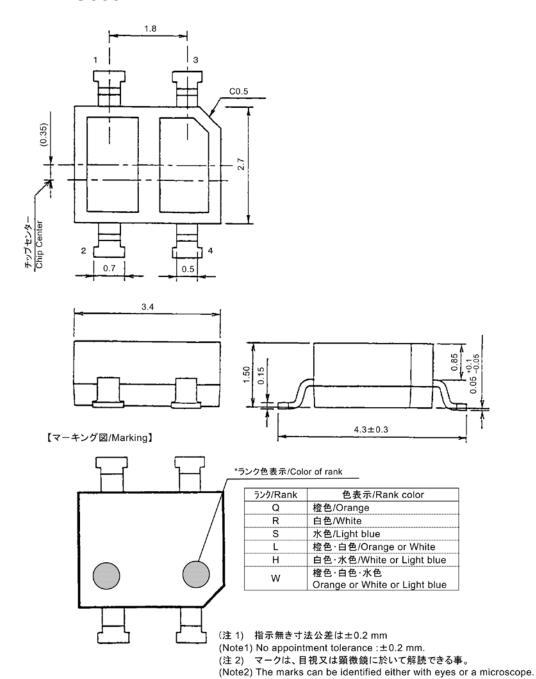


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■ Package (Unit: mm)

LSMFRN4G0001



- Pin name
 - 1: Anode
 - 2: Cathode
 - 3: Emitter
 - 4: Collector

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